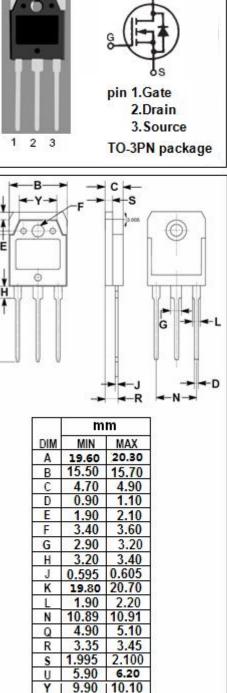


isc N-Channel MOSFET Transistor

TK39J60W

FEATURES · Low drain-source on-resistance: Ros(on) ≤0.065Ω. · Enhancement mode: Vth =2.7 to 3.7V (VDs = 10 V, ID=1.9mA) • 100% avalanche tested · Minimum Lot-to-Lot variations for robust device performance and reliable operation 1 2 3 DESCRITION Switching Voltage Regulators ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL VALUE UNIT PARAMETER ė V_{DSS} **Drain-Source Voltage** 600 V Gate-Source Voltage V V_{GS} ± 30 I_D **Drain Current-Continuous** 38.8 А Drain Current-Single Pulsed 155 **I**DM А DIM MIN A В P_D Total Dissipation @Tc=25°C 270 W C 4.70 D 0.90E 1.90 Max. Operating Junction Temperature 150 °C Tj F 3.40G 2.90н 20 Storage Temperature -55~150 °C Tstg J 0 595 κ Ν 10.89 THERMAL CHARACTERISTICS 4.90Q R 3.35SYMBOL PARAMETER MAX UNIT .995 S



isc website: www.iscsemi.cn

Channel-to-case thermal resistance

Rth(ch-c)

isc & iscsemi is registered trademark

1

0.463

°C/W



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ELECTRICAL CHARACTERISTICS

$T_{\rm C}\text{=}25^\circ\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =10mA	600			v
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =10V; I _D =1.9mA	2.7		3.7	v
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =19.4A			65	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			100	uA
V _{SDF}	Diode forward voltage	I _{DR} =38.8A, V _{GS} = 0 V			1.7	V



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